

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	27mΩ@10V	5.8A
	30mΩ@4.5V	
	40mΩ@2.5V	

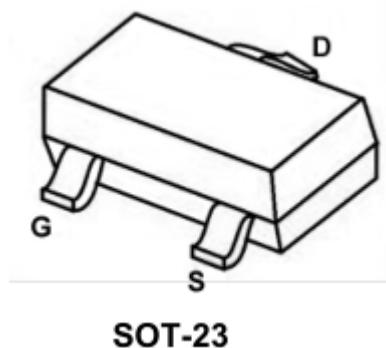
Feature

- TrenchFET Power MOSFET
- Excellent RDS(on) and Low Gate Charge

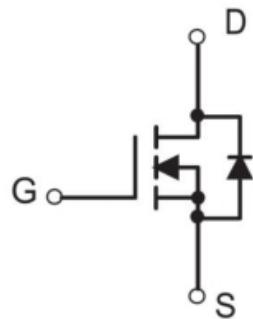
Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

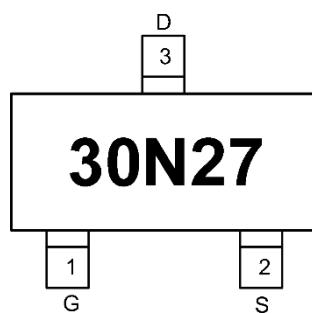
Package



Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current ¹	I_{DM}	30	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

Electrical characteristics

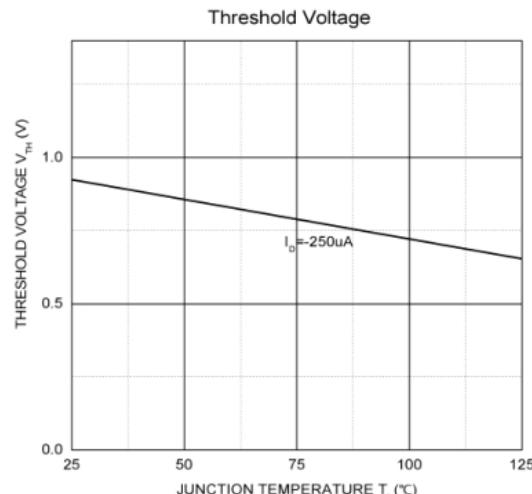
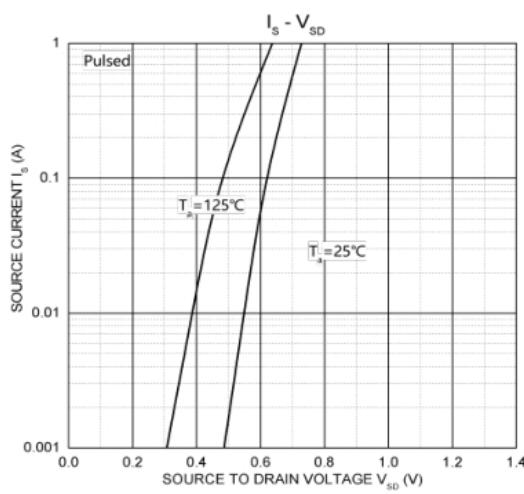
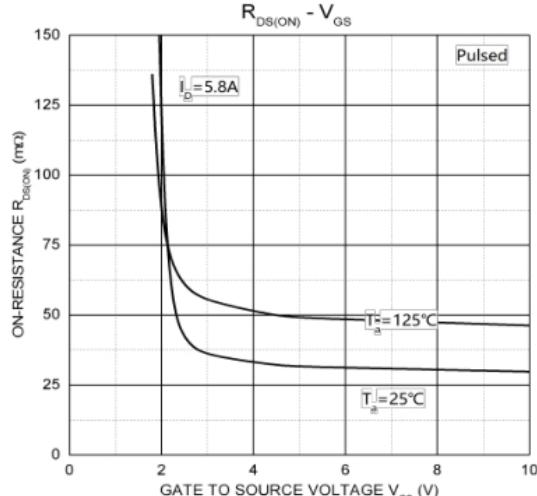
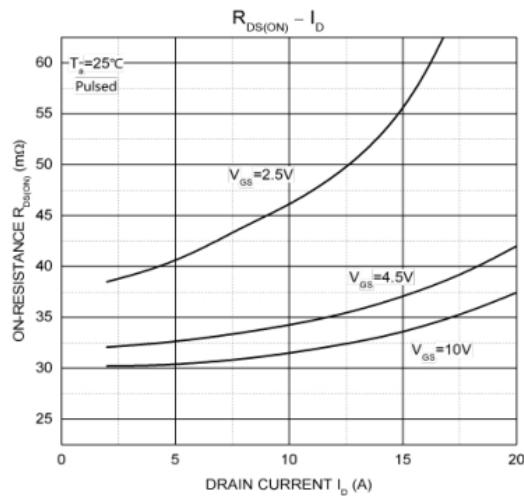
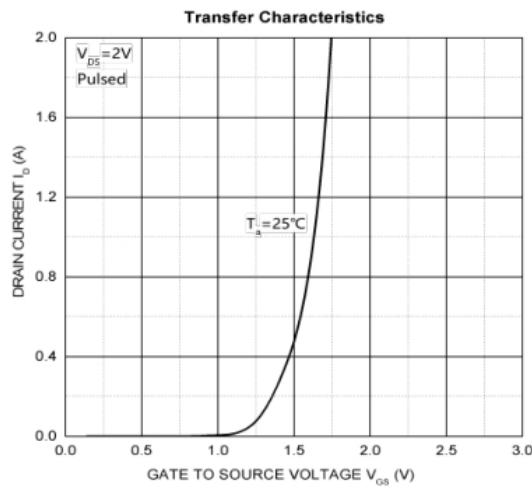
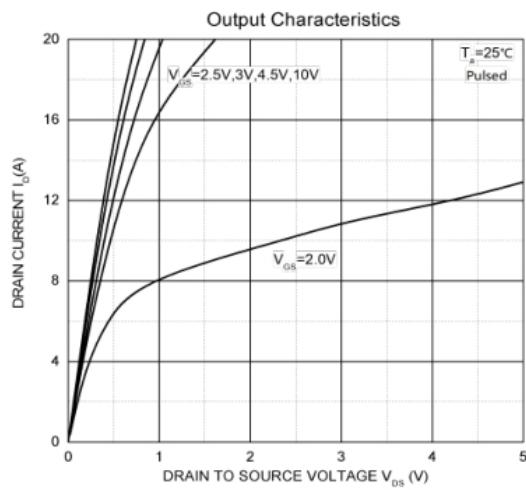
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 0.1	μA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.7		1.4	V
Drain-Source On-Resistance ²	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 5.8\text{A}$		27	35	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 5\text{A}$		30	40	
		$V_{GS} = 2.5\text{V}, I_D = 4\text{A}$		40	50	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$			1050	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$			3.6	Ω
Switching Characteristics						
Turn-on Delay Time	$T_{d(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, R_L = 2.7\Omega, R_{GEN} = 3\Omega$			5	nS
Turn-on Rise Time	T_r				7	
Turn-off Delay Time	$T_{d(off)}$				40	
Turn-off Fall Time	T_f				6	
Source-Drain Diode Characteristics						
Body Diode Voltage ³	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		07	1.3	V

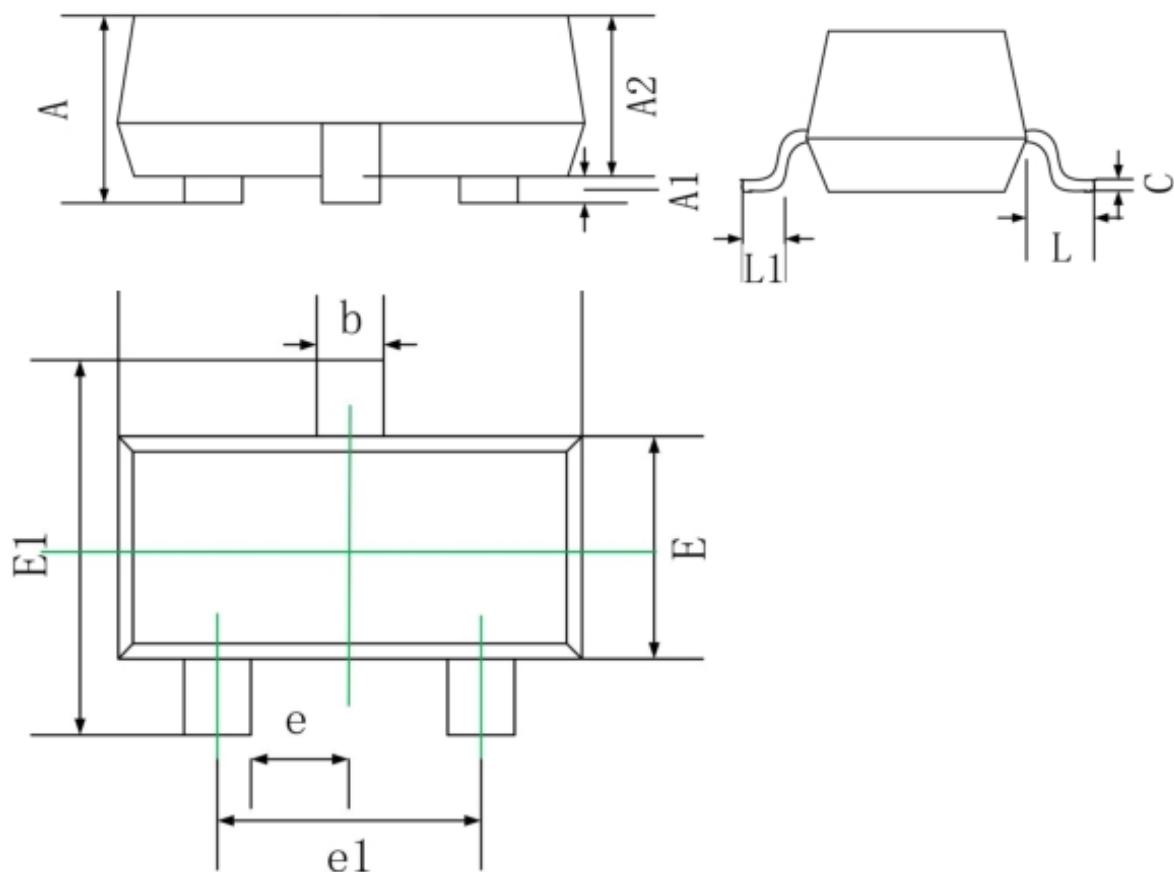
Note:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t < 5$ sec.
3. Pulse Test : Pulse Width $\leqslant 300\mu\text{s}$, Duty Cycle $\leqslant 2\%$.
4. Guaranteed by design, not subject to production testing.

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50